

Form PTO-1449
(Rev. 8-83)U.S. Department of Commerce
Patent and Trademark Office

Attorney Docket No. 0756-1984

Serial No. Not Yet Assigned

INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

Applicant: Shunpei YAMAZAKI et al.

Filing Date: June 17, 1999

Group: 2811

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| Examiner Initial | Patent Number | Date | Name | Class | Subclass | Filing Date (if appropriate) |
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Examiner

Shunpei Yamazaki

Date Considered

12-14-99

*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.